74AUP1G98

Low-power configurable multiple function gate

Rev. 8 — 23 September 2015 Product data sheet

1. General description

The 74AUP1G98 provides configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions MUX, AND, OR, NAND, NOR, inverter and buffer. All inputs can be connected to V_{CC} or GND.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF}.
The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74AUP1G98 has Schmitt trigger inputs making it capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
  - HBM JESD22-A114F exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation
- Multiple package options
- Specified from −40 °C to +85 °C and −40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G98GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74AUP1G98GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AUP1G98GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891
74AUP1G98GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm	SOT1115
74AUP1G98GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm	SOT1202
74AUP1G98GX	–40 °C to +125 °C	X2SON6	plastic thermal extremely thin small outline package; no leads; 6 terminals; body 1 × 0.8 × 0.35 mm	SOT1255

4. Marking

Table 2. Marking

Type number	Marking code[1]
74AUP1G98GW	a9
74AUP1G98GM	a9
74AUP1G98GF	a9
74AUP1G98GN	a9
74AUP1G98GS	a9
74AUP1G98GX	a9

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

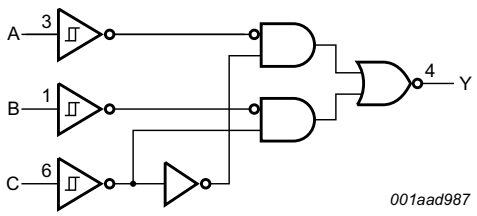


Fig 1. Logic diagram

6. Pinning information

6.1 Pinning

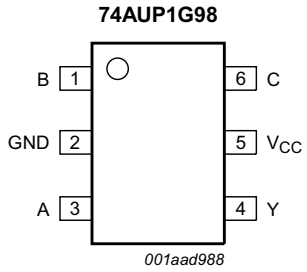


Fig 2. Pin configuration SOT363

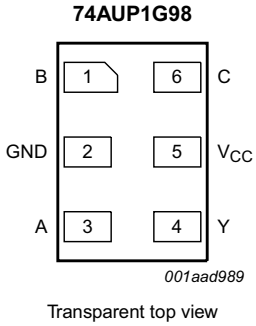


Fig 3. Pin configuration SOT886

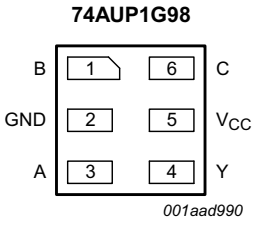


Fig 4. Pin configuration SOT891, SOT1115 and SOT1202

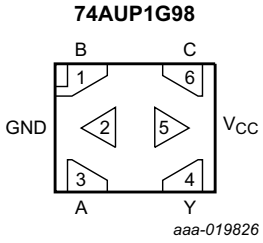


Fig 5. Pin configuration SOT1255 (X2SON6)

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B	1	data input
GND	2	ground (0 V)
A	3	data input
Y	4	data output
V_{CC}	5	supply voltage
C	6	data input

7. Functional description

Table 4. Function table[1]

Input			Output
C	**B**	**A**	**Y**
L	L	L	H
L	L	H	H
L	H	L	L
L	H	H	L
H	L	L	H
H	L	H	L
H	H	L	H
H	H	H	L

[1] H = HIGH voltage level;
L = LOW voltage level.

7.1 Logic configurations

Table 5. Function selection table

Logic function	Figure
2-input MUX with inverted output	see Figure 6
2-input NAND	see Figure 7
2-input NOR with one input inverted	see Figure 8
2-input AND with one input inverted	see Figure 8
2-input NAND with one input inverted	see Figure 9
2-input OR with one input inverted	see Figure 9
2-input NOR	see Figure 10
Buffer	see Figure 11
Inverter	see Figure 12

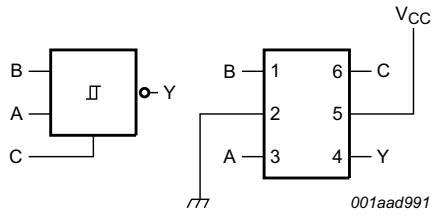


Fig 6. 2-input MUX with inverted output

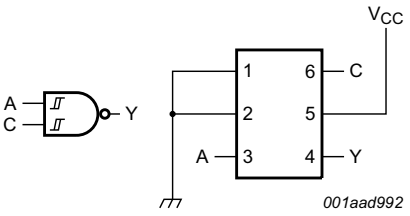


Fig 7. 2-input NAND gate

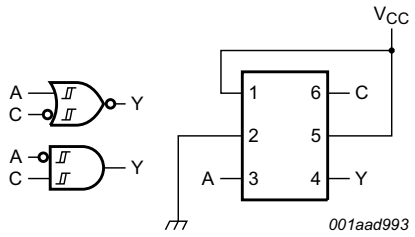


Fig 8. 2-input AND gate with input A inverted or 2-input NOR gate with inverted C input

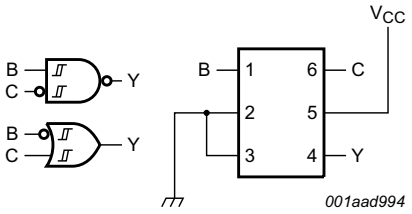


Fig 9. 2-input OR gate with input B inverted or 2-input NAND gate with input C inverted

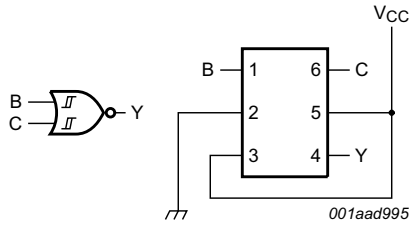


Fig 10. 2-input NOR gate

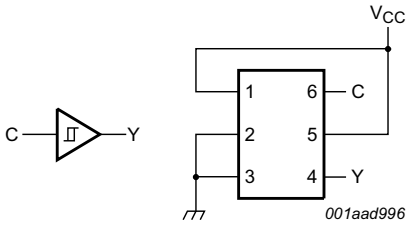


Fig 11. Buffer

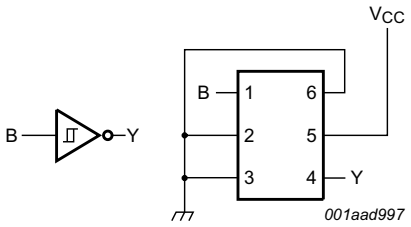


Fig 12. Inverter

8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		–0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	–50	-	mA
V_I	input voltage	[1]	–0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0$ V	–50	-	mA
V_O	output voltage	Active mode and Power-down mode [1]	–0.5	+4.6	V
I_O	output current	V_O = 0 V to V_{CC}	-	±20	mA
I_{CC}	supply current		-	50	mA

Table 6. Limiting values *...continued*

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
I_{GND}	ground current		–50	-	mA
T_{stg}	storage temperature		–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C [2]	-	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For X2SON6 and XSON6 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 7. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; V_{CC} = 0 V	0	3.6	V
T_{amb}	ambient temperature		–40	+125	°C

10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = –20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} – 0.1	-	-	V
		I_O = –1.1 mA; V_{CC} = 1.1 V	0.75V_{CC}	-	-	V
		I_O = –1.7 mA; V_{CC} = 1.4 V	1.11	-	-	V
		I_O = –1.9 mA; V_{CC} = 1.65 V	1.32	-	-	V
		I_O = –2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		I_O = –3.1 mA; V_{CC} = 2.3 V	1.9	-	-	V
		I_O = –2.7 mA; V_{CC} = 3.0 V	2.72	-	-	V
		I_O = –4.0 mA; V_{CC} = 3.0 V	2.6	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	0.3V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.31	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.31	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.31	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.44	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.31	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.44	V

Table 8. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	-	-	±0.2	μA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.5	μA
ΔI_{CC}	additional supply current	V_I = V_{CC} − 0.6 V; I_O = 0 A; V_{CC} = 3.3 V [1]	-	-	40	μA
C_I	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}	-	1.1	-	pF
C_O	output capacitance	V_O = GND; V_{CC} = 0 V	-	1.7	-	pF
T_{amb} = −40 °C to +85 °C						
V_{OH}	HIGH-level output voltage	V_I = V_{T+} or V_{T-}				
		I_O = −20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} − 0.1	-	-	V
		I_O = −1.1 mA; V_{CC} = 1.1 V	0.7V_{CC}	-	-	V
		I_O = −1.7 mA; V_{CC} = 1.4 V	1.03	-	-	V
		I_O = −1.9 mA; V_{CC} = 1.65 V	1.30	-	-	V
		I_O = −2.3 mA; V_{CC} = 2.3 V	1.97	-	-	V
		I_O = −3.1 mA; V_{CC} = 2.3 V	1.85	-	-	V
		I_O = −2.7 mA; V_{CC} = 3.0 V	2.67	-	-	V
		I_O = −4.0 mA; V_{CC} = 3.0 V	2.55	-	-	V
V_{OL}	LOW-level output voltage	V_I = V_{T+} or V_{T-}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	0.3V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.37	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.33	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V
I_I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.5	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	-	-	±0.6	μA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI_{CC}	additional supply current	V_I = V_{CC} − 0.6 V; I_O = 0 A; V_{CC} = 3.3 V [1]	-	-	50	μA

Table 8. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = –40 °C to +125 °C						
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = –20 μA; V_{CC} = 0.8 V to 3.6 V	V_{CC} – 0.11	-	-	V
		I_O = –1.1 mA; V_{CC} = 1.1 V	0.6V_{CC}	-	-	V
		I_O = –1.7 mA; V_{CC} = 1.4 V	0.93	-	-	V
		I_O = –1.9 mA; V_{CC} = 1.65 V	1.17	-	-	V
		I_O = –2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		I_O = –3.1 mA; V_{CC} = 2.3 V	1.67	-	-	V
		I_O = –2.7 mA; V_{CC} = 3.0 V	2.40	-	-	V
		I_O = –4.0 mA; V_{CC} = 3.0 V	2.30	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = 20 μA; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I_O = 1.1 mA; V_{CC} = 1.1 V	-	-	0.33V_{CC}	V
		I_O = 1.7 mA; V_{CC} = 1.4 V	-	-	0.41	V
		I_O = 1.9 mA; V_{CC} = 1.65 V	-	-	0.39	V
		I_O = 2.3 mA; V_{CC} = 2.3 V	-	-	0.36	V
		I_O = 3.1 mA; V_{CC} = 2.3 V	-	-	0.50	V
		I_O = 2.7 mA; V_{CC} = 3.0 V	-	-	0.36	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.50	V
I_I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.75	μA
ΔI_{OFF}	additional power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V to 0.2 V	-	-	±0.75	μA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6$ V; I_O = 0 A; V_{CC} = 3.3 V [1]	-	-	75	μA

[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 14.

Symbol	Parameter	Conditions	T_{amb} = 25 °C			T_{amb} = –40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 5 pF									
t_{pd}	propagation delay	A, B, C to Y; see Figure 13 [2]							
		V_{CC} = 0.8 V	-	23.3	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	2.9	6.7	12.9	2.7	13.2	13.4	ns
		V_{CC} = 1.4 V to 1.6 V	2.4	4.8	7.7	2.4	8.3	8.7	ns
		V_{CC} = 1.65 V to 1.95 V	2.2	4.0	6.3	1.9	7.0	7.4	ns
		V_{CC} = 2.3 V to 2.7 V	2.0	3.2	4.6	1.8	5.2	5.4	ns
		V_{CC} = 3.0 V to 3.6 V	1.9	2.9	4.0	1.6	4.2	4.4	ns
C_L = 10 pF									
t_{pd}	propagation delay	A, B, C to Y; see Figure 13 [2]							
		V_{CC} = 0.8 V	-	27.1	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	3.3	7.6	14.5	3.0	15.1	15.3	ns
		V_{CC} = 1.4 V to 1.6 V	2.7	5.4	8.8	2.8	9.5	9.9	ns
		V_{CC} = 1.65 V to 1.95 V	2.5	4.6	7.2	2.3	8.0	8.4	ns
		V_{CC} = 2.3 V to 2.7 V	2.4	3.8	5.3	2.2	5.9	6.2	ns
		V_{CC} = 3.0 V to 3.6 V	2.3	3.5	4.7	2.0	4.9	5.2	ns
C_L = 15 pF									
t_{pd}	propagation delay	A, B, C to Y; see Figure 13 [2]							
		V_{CC} = 0.8 V	-	30.6	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	3.6	8.4	16.1	3.3	16.9	17.2	ns
		V_{CC} = 1.4 V to 1.6 V	3.0	6.0	9.7	3.1	10.5	11.0	ns
		V_{CC} = 1.65 V to 1.95 V	2.8	5.1	7.9	2.5	8.9	9.3	ns
		V_{CC} = 2.3 V to 2.7 V	2.7	4.2	5.9	2.5	6.6	7.0	ns
		V_{CC} = 3.0 V to 3.6 V	2.5	3.9	5.2	2.2	5.5	5.8	ns

Table 9. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 14.

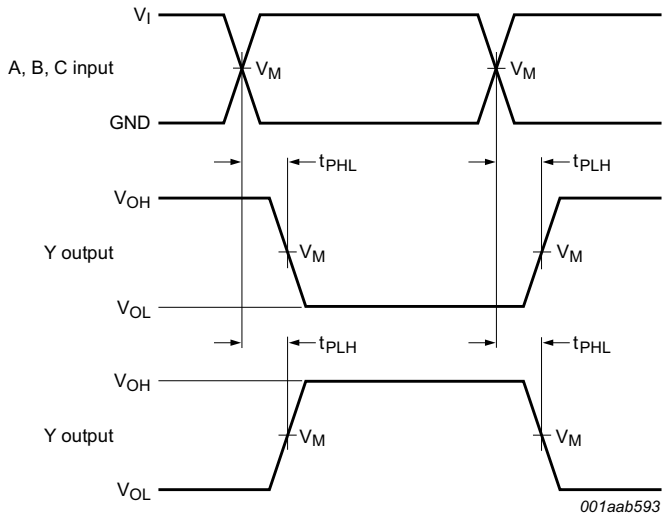
Symbol	Parameter	Conditions	T_{amb} = 25 °C			T_{amb} = –40 °C to +125 °C			Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C_L = 30 pF									
t_{pd}	propagation delay	A, B, C to Y; see Figure 13 [2]							
		V_{CC} = 0.8 V	-	38.7	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	4.5	10.7	21.1	4.1	22.0	22.4	ns
		V_{CC} = 1.4 V to 1.6 V	3.8	7.6	12.3	3.8	13.5	14.2	ns
		V_{CC} = 1.65 V to 1.95 V	3.5	6.3	10.1	3.1	11.3	11.9	ns
		V_{CC} = 2.3 V to 2.7 V	3.4	5.3	7.5	3.2	8.4	8.9	ns
		V_{CC} = 3.0 V to 3.6 V	3.2	5.0	6.7	2.9	7.1	7.5	ns
C_L = 5 pF, 10 pF, 15 pF and 30 pF									
C_{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC} [3]							
		V_{CC} = 0.8 V	-	2.7	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V	-	2.9	-	-	-	-	pF
		V_{CC} = 1.4 V to 1.6 V	-	3.0	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V	-	3.2	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	3.8	-	-	-	-	pF
		V_{CC} = 3.0 V to 3.6 V	-	4.4	-	-	-	-	pF

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



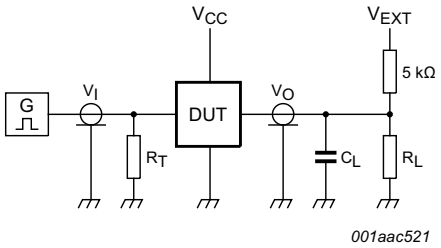
Measurement points are given in Table 10.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 13. Input A, B and C to output Y propagation delay times.

Table 10. Measurement points

Supply voltage	Output	Input		
V_{CC}	V_M	V_M	V_I	$t_r = t_f$
0.8 V to 3.6 V	$0.5V_{CC}$	$0.5V_{CC}$	V_{CC}	≤ 3.0 ns



Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 14. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L[1]	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2V_{CC}$

[1] For measuring enable and disable times R_L = 5 kΩ, for measuring propagation delays, setup and hold times and pulse width R_L = 1 MΩ.

13. Transfer characteristics

Table 12. Transfer characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 14.

Symbol	Parameter	Conditions	T_{amb} = 25 °C			T_{amb} = –40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V_{T+}	positive-going threshold voltage	see Figure 15 and Figure 16							
		V_{CC} = 0.8 V	0.30	-	0.60	0.30	0.60	0.62	V
		V_{CC} = 1.1 V	0.53	-	0.90	0.53	0.90	0.92	V
		V_{CC} = 1.4 V	0.74	-	1.11	0.74	1.11	1.13	V
		V_{CC} = 1.65 V	0.91	-	1.29	0.91	1.29	1.31	V
		V_{CC} = 2.3 V	1.37	-	1.77	1.37	1.77	1.80	V
		V_{CC} = 3.0 V	1.88	-	2.29	1.88	2.29	2.32	V
V_{T-}	negative-going threshold voltage	see Figure 15 and Figure 16							
		V_{CC} = 0.8 V	0.10	-	0.60	0.10	0.60	0.60	V
		V_{CC} = 1.1 V	0.26	-	0.65	0.26	0.65	0.65	V
		V_{CC} = 1.4 V	0.39	-	0.75	0.39	0.75	0.75	V
		V_{CC} = 1.65 V	0.47	-	0.84	0.47	0.84	0.84	V
		V_{CC} = 2.3 V	0.69	-	1.04	0.69	1.04	1.04	V
		V_{CC} = 3.0 V	0.88	-	1.24	0.88	1.24	1.24	V

Table 12. Transfer characteristics *…continued*

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 14.

Symbol	Parameter	Conditions	T_{amb} = 25 °C			T_{amb} = –40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V_H	hysteresis voltage	(V_{T+} – V_{T-}); see Figure 15, Figure 16, Figure 17 and Figure 18							
		V_{CC} = 0.8 V	0.07	-	0.50	0.07	0.50	0.50	V
		V_{CC} = 1.1 V	0.08	-	0.46	0.08	0.46	0.46	V
		V_{CC} = 1.4 V	0.18	-	0.56	0.18	0.56	0.56	V
		V_{CC} = 1.65 V	0.27	-	0.66	0.27	0.66	0.66	V
		V_{CC} = 2.3 V	0.53	-	0.92	0.53	0.92	0.92	V
		V_{CC} = 3.0 V	0.79	-	1.31	0.79	1.31	1.31	V

14. Waveforms transfer characteristics

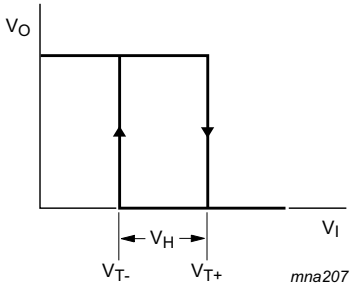
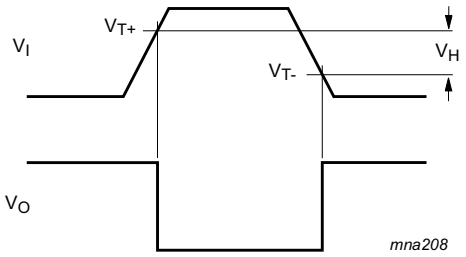


Fig 15. Transfer characteristic



V_{T+} and V_{T-} limits at 70 % and 20 %.

Fig 16. Definition of V_{T+}, V_{T-} and V_H

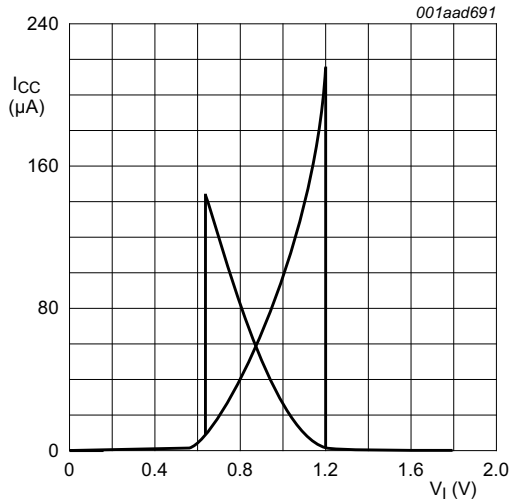


Fig 17. Typical transfer characteristics; V_{CC} = 1.8 V

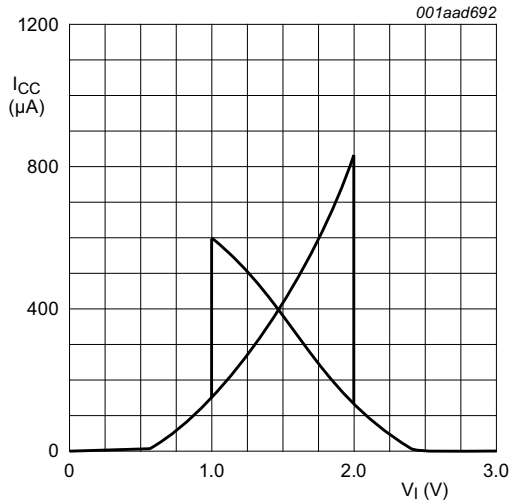
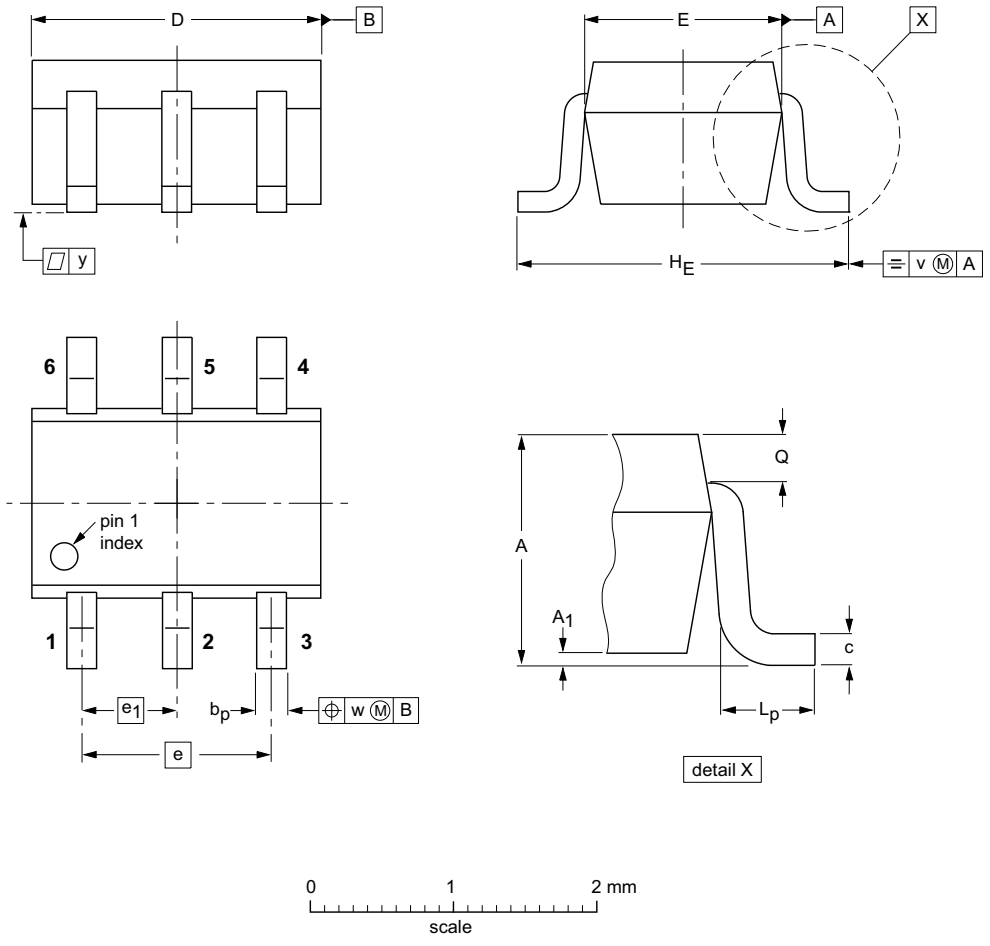


Fig 18. Typical transfer characteristics; V_{CC} = 3.0 V

15. Package outline

Plastic surface-mounted package; 6 leads **SOT363**



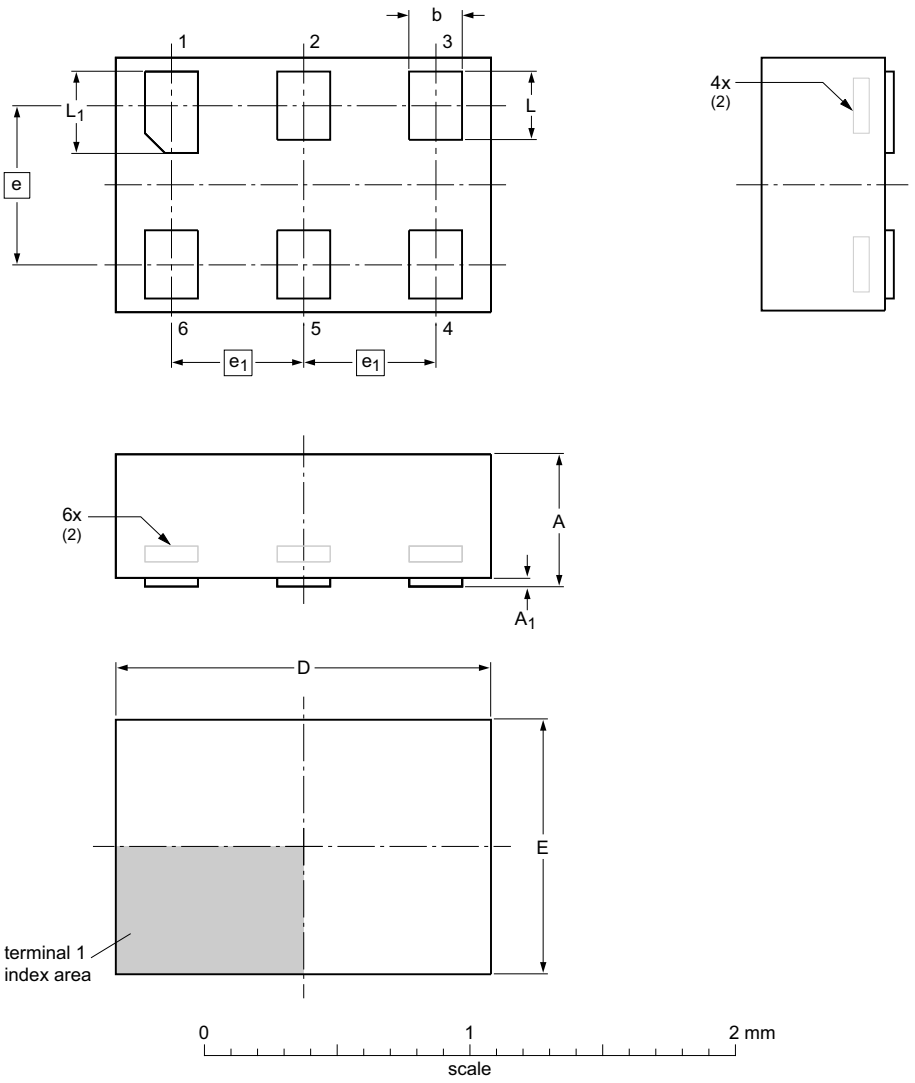
DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			~~04-11-08~~ 06-03-16

Fig 19. Package outline SOT363 (SC-88)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm SOT886



Dimensions (mm are the original dimensions)

Unit		A(1)	A_1	b	D	E	e	e_1	L	L_1
mm	max	0.5	0.04	0.25	1.50	1.05			0.35	0.40
	nom			0.20	1.45	1.00	0.6	0.5	0.30	0.35
	min			0.17	1.40	0.95			0.27	0.32

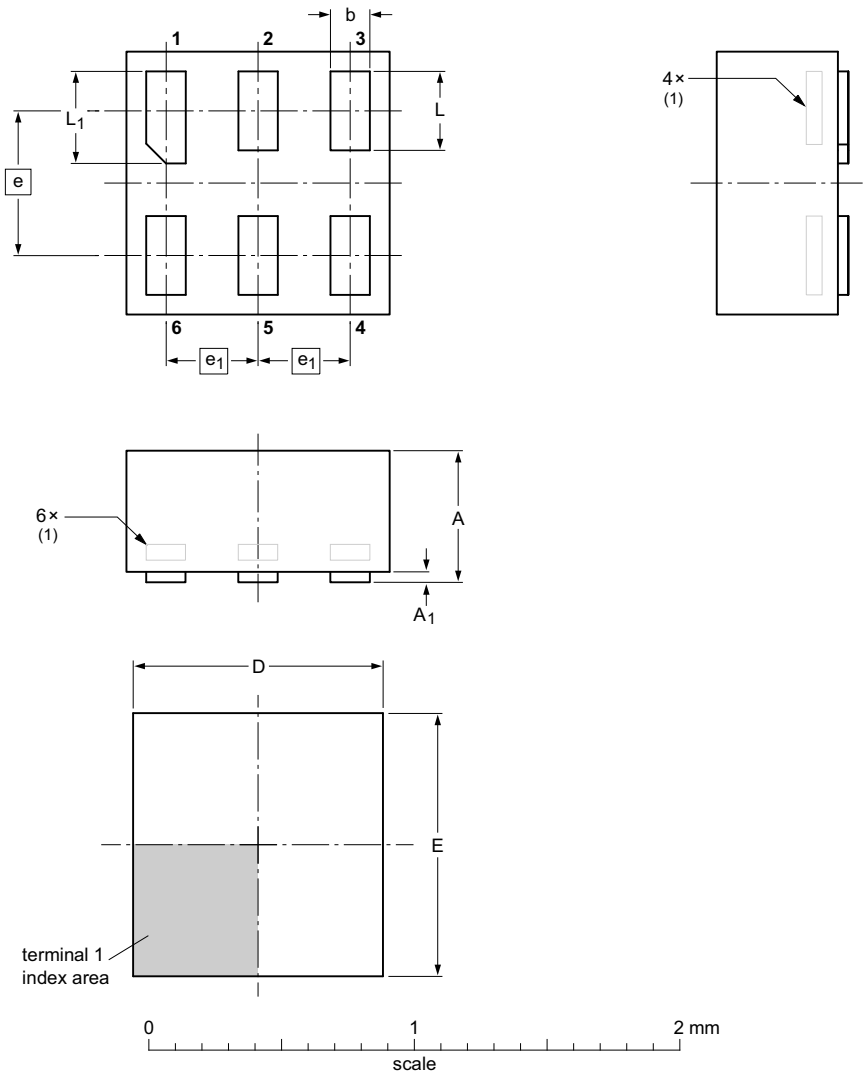
Notes
1. Including plating thickness.
2. Can be visible in some manufacturing processes.

sot886_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT886		MO-252				~~04-07-22~~ 12-01-05

Fig 20. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm **SOT891**



DIMENSIONS (mm are the original dimensions)

UNIT	A max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.20 0.12	1.05 0.95	1.05 0.95	0.55	0.35	0.35 0.27	0.40 0.32

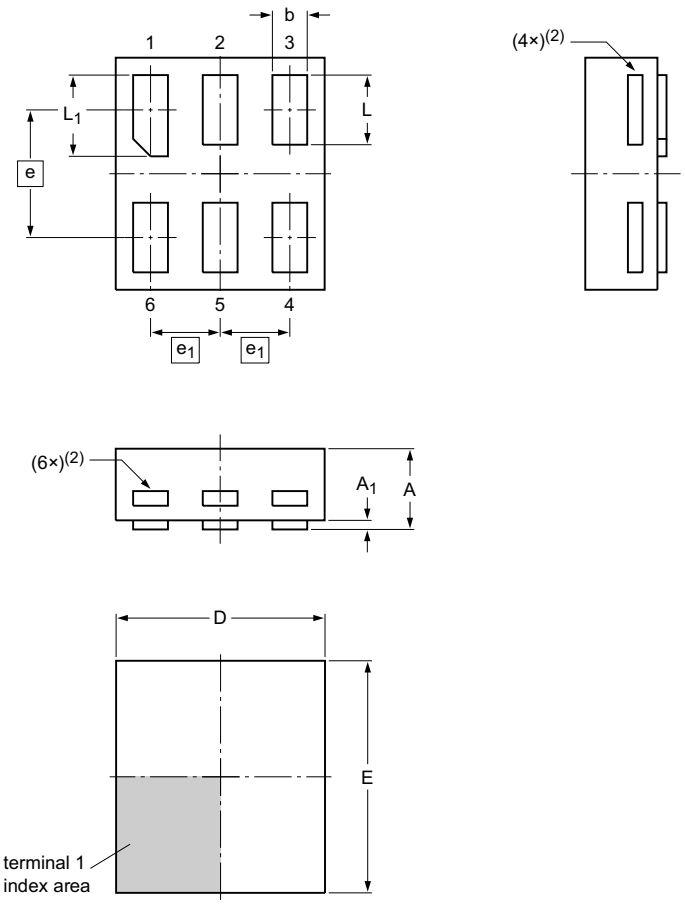
Note

1. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT891						~~05-04-06~~ 07-05-15

Fig 21. Package outline SOT891 (XSON6)

XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm **SOT1115**



Dimensions

Unit		$A^{(1)}$	A_1	b	D	E	e	e_1	L	L_1
mm	max	0.35	0.04	0.20	0.95	1.05			0.35	0.40
	nom			0.15	0.90	1.00	0.55	0.3	0.30	0.35
	min			0.12	0.85	0.95			0.27	0.32

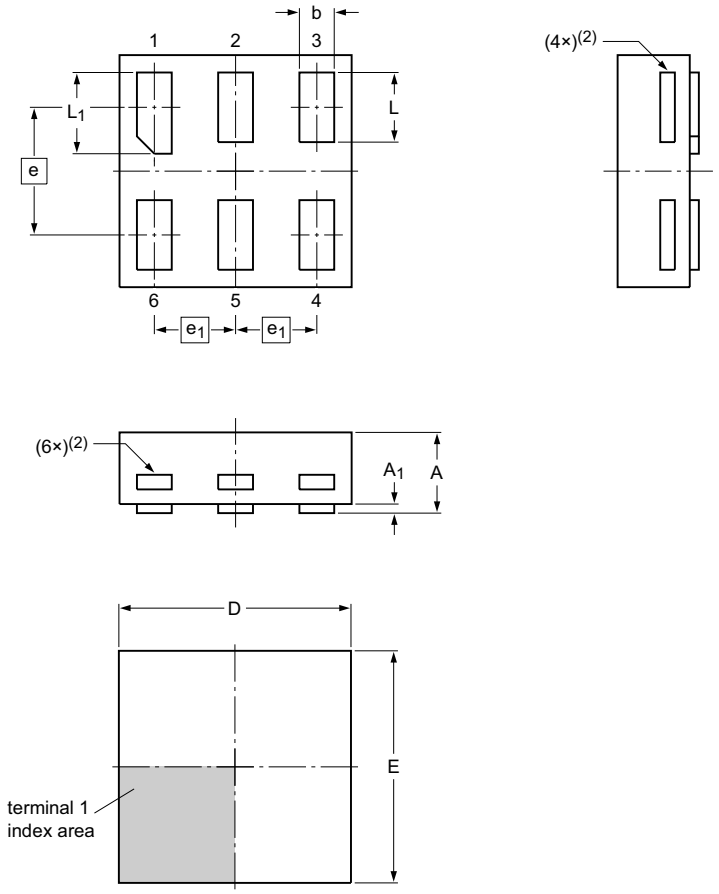
Note
1. Including plating thickness.
2. Visible depending upon used manufacturing technology.

sot1115_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1115						~~10-04-02~~ 10-04-07

Fig 22. Package outline SOT1115 (XSON6)

XSON6: extremely thin small outline package; no leads;
6 terminals; body 1.0 x 1.0 x 0.35 mm **SOT1202**



Dimensions

Unit		A(1)	A_1	b	D	E	e	e_1	L	L_1
mm	max	0.35	0.04	0.20	1.05	1.05			0.35	0.40
	nom			0.15	1.00	1.00	0.55	0.35	0.30	0.35
	min			0.12	0.95	0.95			0.27	0.32

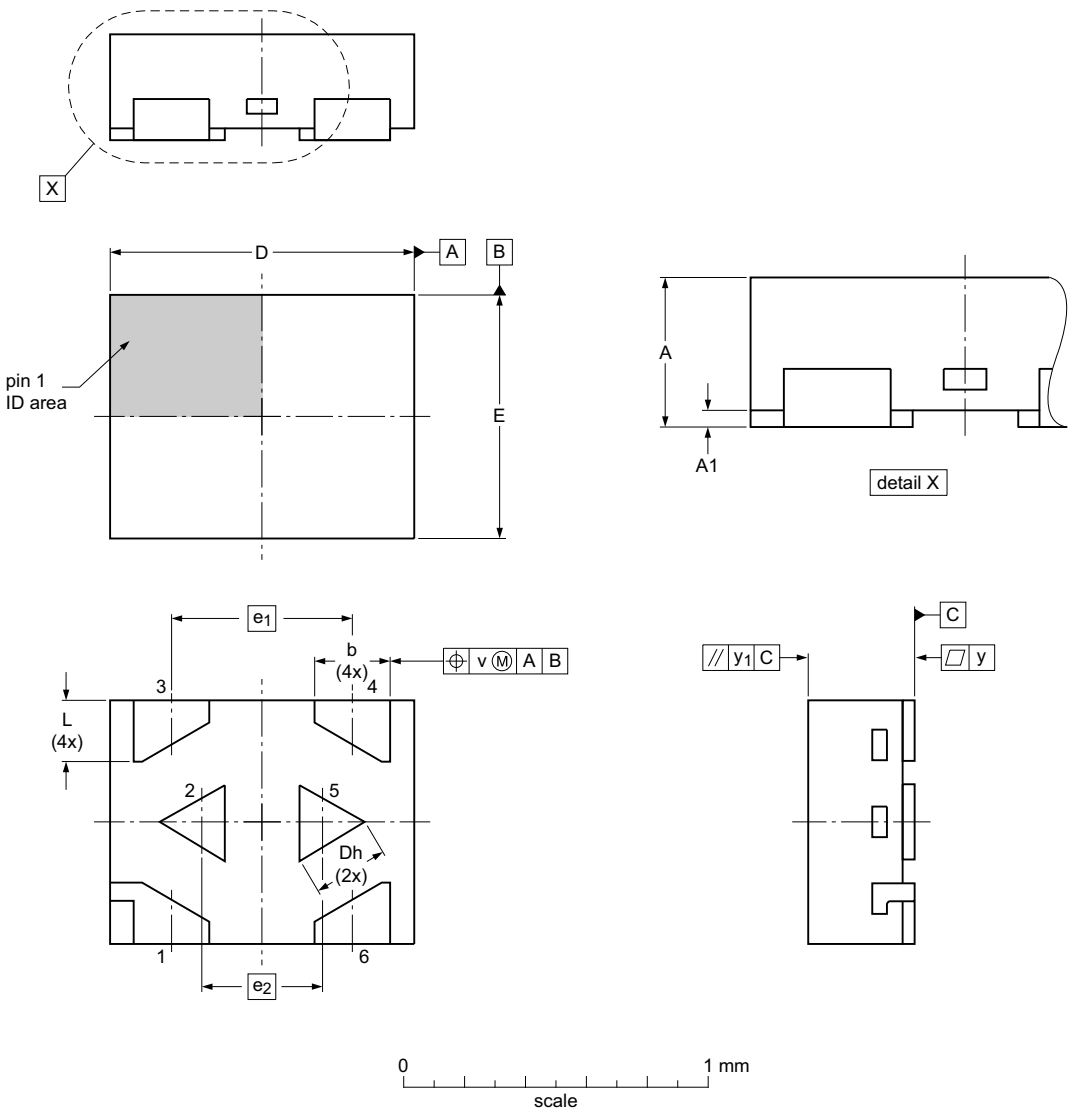
Note
1. Including plating thickness.
2. Visible depending upon used manufacturing technology.

sot1202_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1202						~~10-04-02~~ 10-04-06

Fig 23. Package outline SOT1202 (XSON6)

X2SON6: plastic thermal enhanced extremely thin small outline package; no leads; 6 terminals; body 1.0 x 0.8 x 0.35 mm **SOT1255**



Dimensions (mm are the original dimensions)

Unit	A	A_1	D	D_h	E	e_1	e_2	b	L	v	y	y_1
max	0.35	0.04	1.05	0.30	0.85			0.30	0.25			
mm nom	0.32	0.02	1.00	0.25	0.80	0.60	0.40	0.25	0.20	0.10	0.05	0.05
min	0.30	0.00	0.95	0.22	0.75			0.22	0.17			

sot1255_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1255						~~15-07-20~~ 15-07-22

Fig 24. Package outline SOT1255 (X2SON6)

16. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

17. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G98 v.8	20150923	Product data sheet	-	74AUP1G98 v.7
Modifications:	• Added type number 74AUP1G98GX (SOT1255/X2SON6).			
74AUP1G98 v.7	20120815	Product data sheet	-	74AUP1G98 v.6
Modifications:	• Package outline drawing of SOT886 (Figure 20) modified.			
74AUP1G98 v.6	20111128	Product data sheet	-	74AUP1G98 v.5
74AUP1G98 v.5	20110105	Product data sheet	-	74AUP1G98 v.4
74AUP1G98 v.4	20101012	Product data sheet	-	74AUP1G98 v.3
74AUP1G98 v.3	20090629	Product data sheet	-	74AUP1G98 v.2
74AUP1G98 v.2	20090402	Product data sheet	-	74AUP1G98 v.1
74AUP1G98 v.1	20061108	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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20. Contents

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